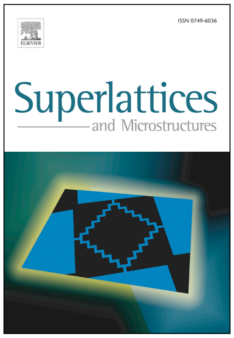

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PII: S0749-6036(16)30869-2

DOI: 10.1016/j.spmi.2016.12.009

Reference: YSPMI 4712

To appear in: *Superlattices and Microstructures*

Received Date: 4 September 2016

Please cite this article as: M.S. Adhikari, Y. Singh, High performance multi-channel MOSFET on InGaAs for RF amplifiers, *Superlattices and Microstructures* (2017), doi: 10.1016/j.spmi.2016.12.009.

Manuscript (YSPMI 4712)

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Submitted to:

Superlattices and Microstructures Journal

04 September 2016